PROCESS BATCH SHEET (ENSC 495/851, 01-1) **Issue 3** **Page_____of_____**

ENSC Batch No.________________________Wafers Started___________Date____________________________
Material________________Orientation________________Size______________Thickness____________________
Resistivity____________________________Type____
Wafer Vendor______________________Vendor Batch #___________________________SFU P.O.____________

Process Step #	**Process Conditions**	**Oper & Wafer #**	**Comments**
_____**A**	RCA clean and Oxidation		
_____**B**	Photolithography 1: define and etch windows in oxide for boron diffusion		
_____**C**	Mod RCA clean and Boron diffusion		
_____**D**	Low Temperature Oxidation		
_____**E**	Oxide strip		
_____**F**	RCA clean, drive-in and oxidation		
_____**G**	Photolithography 2: define and etch windows in oxide for phosphorus diffusion		
_____**H**	RCA clean and Phosphorus diffusion		
_____**I**	Drive-in and oxidation		
_____J	Photolithography 3: define and etch contact cuts for Al		
_____K	Sputter Al (will run only brief demo in class. Class wafers will be sputtered outside of class)		
_____L	Photolithography 4: define and etch aluminum		
____M	Anneal aluminum		
____N	Probe test structures		
____O	Dice and bond		